



MiniSKiiP® 1

3-phase bridge rectifier +  
brake chopper + 3-phase  
bridge inverter

SKiiP 11NAB066V1

## Features

- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

## Typical Applications\*

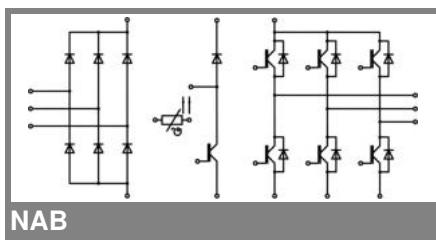
- Inverter up to 3,5 kVA
- Typical motor power 1,5 kW

## Remarks

- Case temperature limited to  $T_C = 125^\circ\text{C}$  max.
- Product reliability results are valid for  $T_j = 150^\circ\text{C}$
- SC data:  $t_p \leq 6 \text{ s}$ ;  $V_{GE} \leq 15 \text{ V}$ ;  $T_j = 150^\circ\text{C}$ ;  $V_{CC} = 360 \text{ V}$
- $V_{CEsat}$ ,  $V_F$  = chip level value

Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT - Inverter, Chopper</b>				
$V_{CES}$		600		V
$I_C$	$T_s = 25 (70)^\circ\text{C}$ , $T_j = 150^\circ\text{C}$	12 (11)		A
$I_C$	$T_s = 25 (70)^\circ\text{C}$ , $T_j = 175^\circ\text{C}$	12 (12)		A
$I_{CRM}$	$t_p = 1 \text{ ms}$	12		A
$V_{GES}$		$\pm 20$		V
<b>Diode - Inverter, Chopper</b>				
$I_F$	$T_s = 25 (70)^\circ\text{C}$ , $T_j = 150^\circ\text{C}$	12 (12)		A
$I_F$	$T_s = 25 (70)^\circ\text{C}$ , $T_j = 175^\circ\text{C}$	12 (12)		A
$I_{FRM}$	$t_p = 1 \text{ ms}$	12		A
<b>Diode - Rectifier</b>				
$V_{RRM}$		800		V
$I_F$	$T_s = 70^\circ\text{C}$	35		A
$I_{FSM}$	$t_p = 10 \text{ ms}$ , $\sin 180^\circ$ , $T_j = 25^\circ\text{C}$	220		A
$i_{\text{t}}$	$t_p = 10 \text{ ms}$ , $\sin 180^\circ$ , $T_j = 25^\circ\text{C}$	240		A <sup>2</sup> s
$I_{FRMS}$	per power terminal (20 A / spring)	20		A
$T_j$	IGBT, Diode	-40...+175		°C
$T_{\text{stg}}$		-40...+125		°C
$V_{\text{isol}}$	AC, 1 min.	2500		V

Characteristics		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
<b>IGBT - Inverter, Chopper</b>				
$V_{CE(\text{sat})}$	$I_{C\text{nom}} = 6 \text{ A}$ , $T_j = 25 (150)^\circ\text{C}$	1,1	1,45 (1,65)	1,85 (2,05)
$V_{GE(\text{th})}$	$V_{CE} = V_{GE}$ , $I_C = 1 \text{ mA}$		5,8	V
$V_{CE(\text{TO})}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,7)	1,1 (1)
$r_{CE}$	$T_j = 25 (150)^\circ\text{C}$		100 (167)	134 (184)
$C_{ies}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		0,45	nF
$C_{oes}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		0,1	nF
$C_{res}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		0,05	nF
$R_{CC'EE'}$	spring contact-chip $T_s = 25 (150)^\circ\text{C}$			mΩ
$R_{th(j-s)}$	per IGBT		2,4	K/W
$t_{d(on)}$	under following conditions		20	ns
$t_r$	$V_{CC} = 300 \text{ V}$ , $V_{GE} = -8\text{V}/+15\text{V}$		25	ns
$t_{d(off)}$	$I_{C\text{nom}} = 6 \text{ A}$ , $T_j = 150^\circ\text{C}$		175	ns
$t_f$	$R_{Gon} = R_{Goff} = 47 \Omega$		60	ns
$E_{on}$ ( $E_{off}$ )	inductive load		0,24 (0,19)	mJ
<b>Diode - Inverter, Chopper</b>				
$V_F = V_{EC}$	$I_F = 6 \text{ A}$ , $T_j = 25 (150)^\circ\text{C}$		1,3 (1,3)	1,6 (1,6)
$V_{(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,8)	1 (0,9)
$r_T$	$T_j = 25 (150)^\circ\text{C}$		67 (83)	100 (117)
$R_{th(j-s)}$	per diode		3	K/W
$I_{RRM}$	under following conditions		11,2	A
$Q_{rr}$	$I_{F\text{nom}} = 6 \text{ A}$ , $V_R = 600 \text{ V}$		0,9	C
$E_{rr}$	$V_{GE} = 0 \text{ V}$ , $T_j = 150^\circ\text{C}$		0,19	mJ
	$di_F/dt = 520 \text{ A/s}$			
<b>Diode - Rectifier</b>				
$V_F$	$I_{F\text{nom}} = 15 \text{ A}$ , $T_j = 25^\circ\text{C}$		1,1	V
$V_{(TO)}$	$T_j = 150^\circ\text{C}$		0,8	V
$r_T$	$T_j = 150^\circ\text{C}$		20	mΩ
$R_{th(j-s)}$	per diode		1,5	K/W
<b>Temperature Sensor</b>				
$R_{ts}$	$3\%$ , $T_r = 25 (100)^\circ\text{C}$		1000(1670)	Ω
<b>Mechanical Data</b>				
$w$		35		g
$M_s$	Mounting torque	2	2,5	Nm



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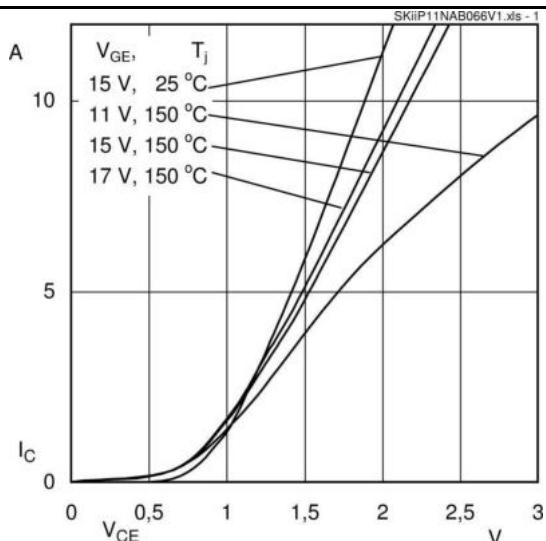


Fig. 1 Typ. output characteristics

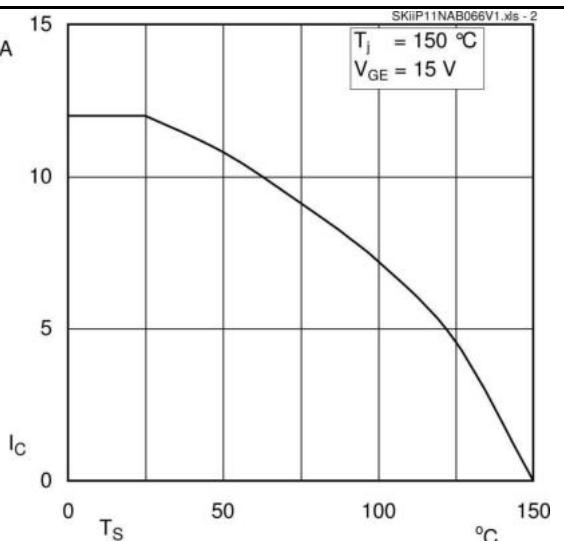


Fig. 2 Typ. rated current vs. temperature

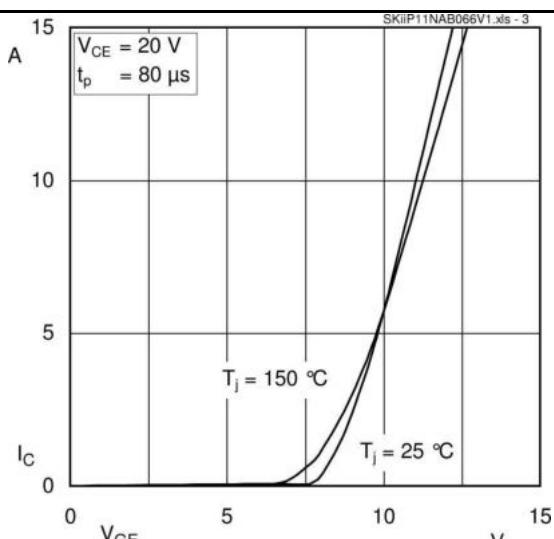


Fig. 3 Typ. transfer characteristic

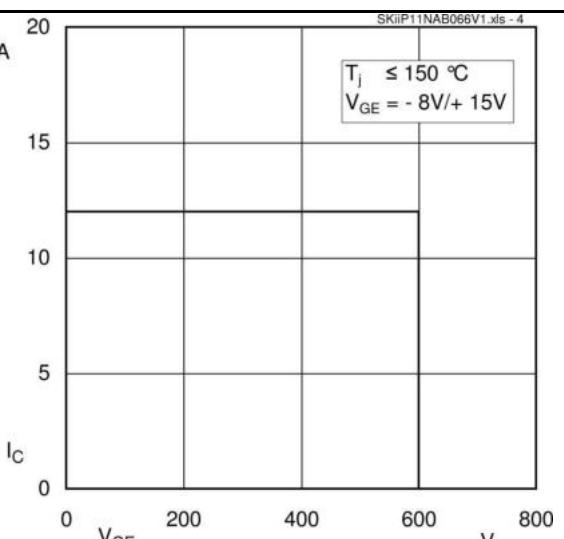


Fig. 4 Reverse bias safe operating area

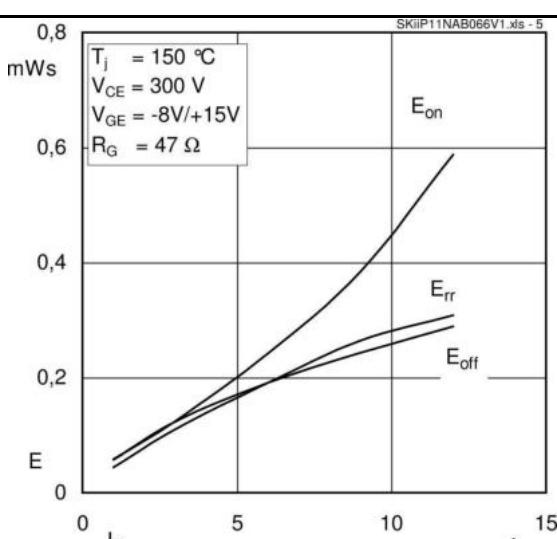


Fig. 5 Typ. Turn-on/-off energy = f ( $I_C$ )

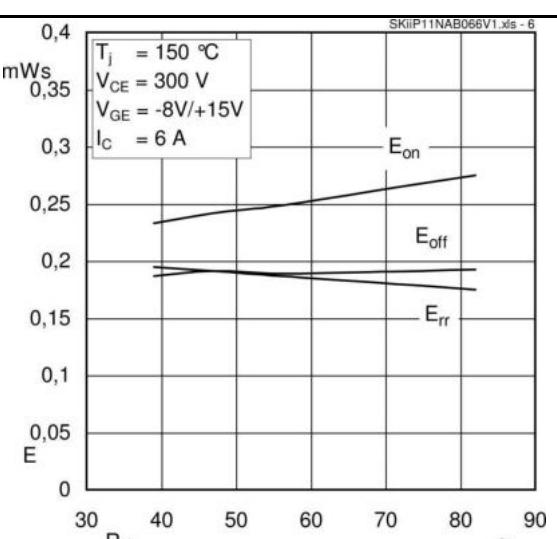


Fig. 6 Typ. Turn-on/-off energy = f ( $R_G$ )

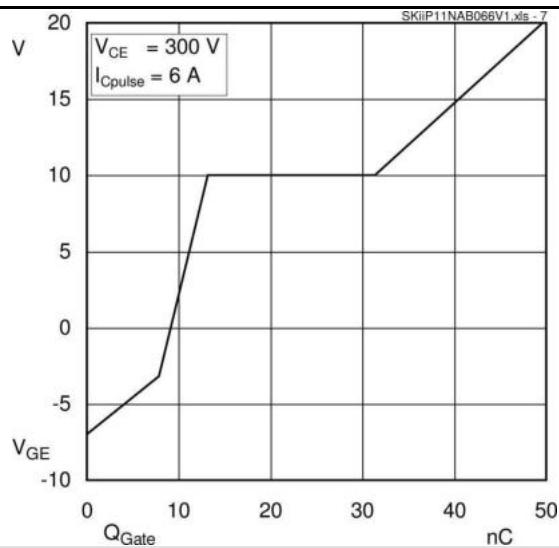


Fig. 7 Typ. gate charge characteristic

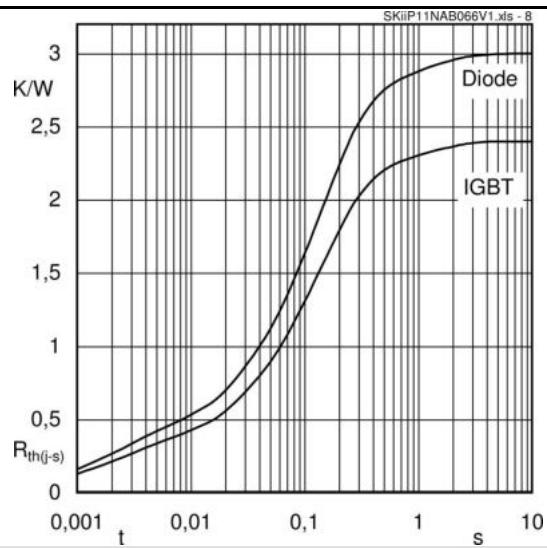


Fig. 8 Typ. thermal impedance

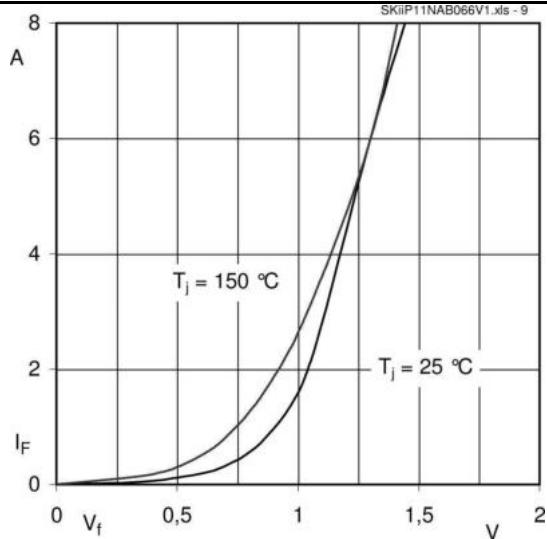


Fig. 9 Typ. freewheeling diode forward characteristic

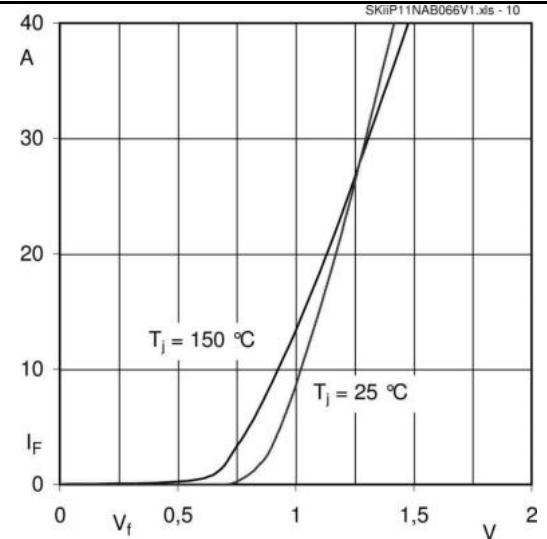
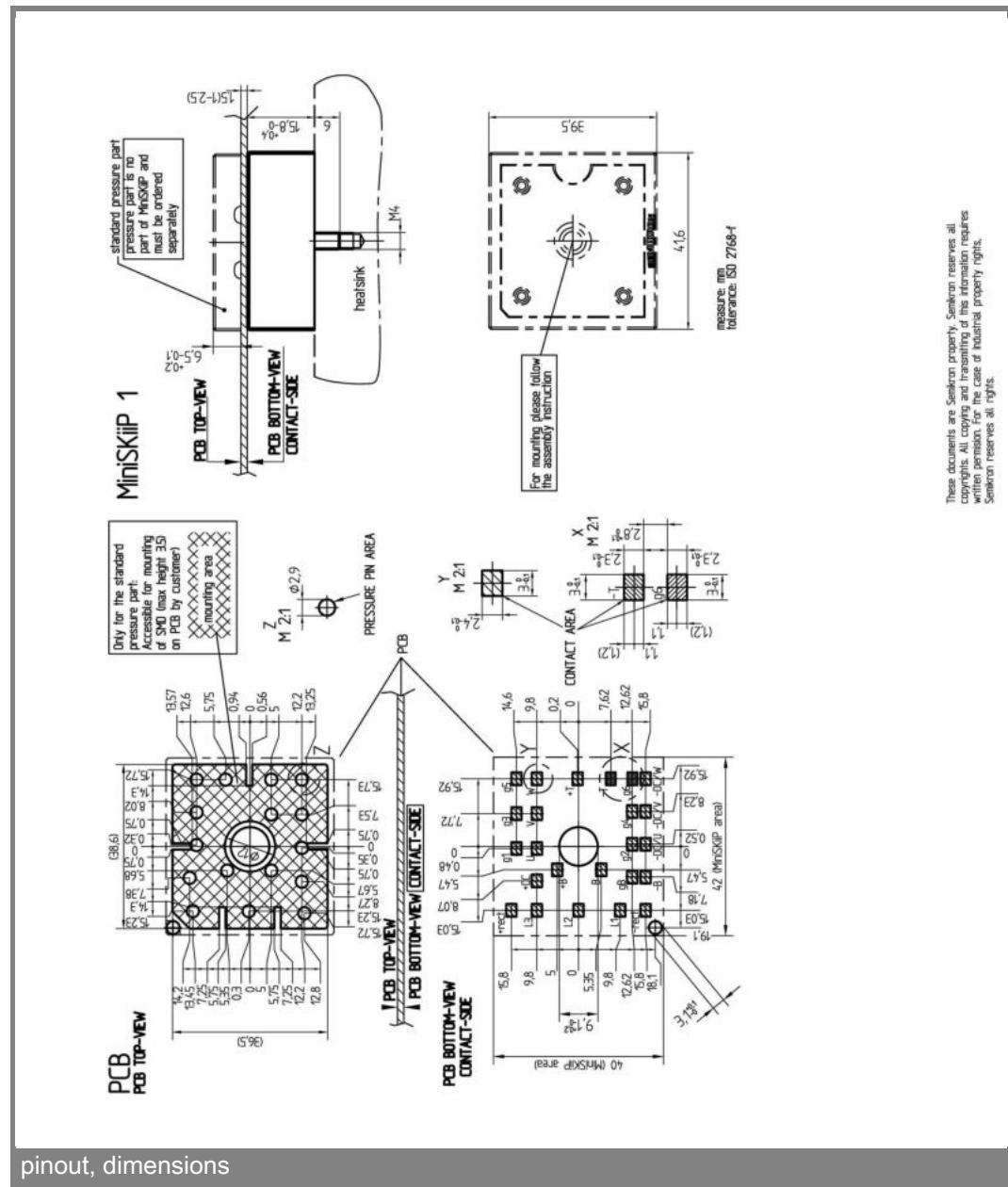
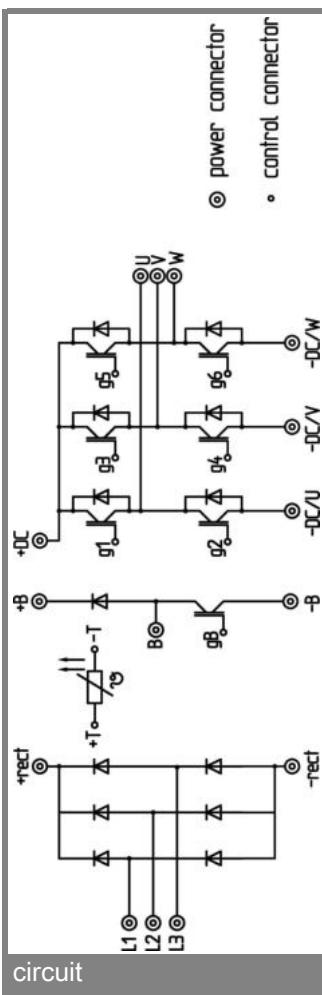


Fig. 10 Typ. input bridge forward characteristic



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

## \*IMPORTANT INFORMATION AND WARNINGS

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